

**Amendments to the Claims:**

This listing of claims will replace all prior versions and listings of claims in the application:

**Listing of Claims:**

1. (Original) A substrate for device bonding, comprising a substrate having an Au electrode layer formed on its surface, wherein (i) a layer composed of a platinum group element, (ii) a layer composed of at least one transition metal element selected from the group consisting of Ti, V, Cr and Co, (iii) a barrier metal layer composed of at least one metal selected from the group consisting of Ag, Cu and Ni and (iv) a solder layer composed of a solder containing Sn or In as a main component are laminated in this order on the Au electrode layer.

2. (Currently Amended) The substrate for device bonding as claimed in claim 1, wherein the solder layer (iv) is composed of ~~a solder~~ said solder containing Sn or In as a main component and having an Au content of less than 20% by weight.

3. (Currently Amended) The substrate for device bonding as claimed in claim 1, wherein the substrate having ~~an Au~~ said Au electrode layer on its surface is a metallized substrate in which a first undercoating metal layer containing Ti as a main component, a second undercoating metal layer containing Pt as a main component and ~~an electrode~~ said electrode layer composed of Au are laminated in this order on a ceramic substrate containing aluminum nitride as a main component.

4. (Original) A process for producing a substrate for device bonding, comprising forming (i) a layer composed of a platinum group element, (ii) a layer composed of at least one transition metal element selected from the group consisting of Ti, V, Cr and Co, (iii) a barrier metal layer composed of at least one metal selected from

the group consisting of Ag, Cu and Ni and (iv) a solder layer composed of a solder containing Sn or In as a main component in this order on an Au electrode layer which is formed on a surface of a substrate.

5. (Currently Amended) The process for producing a substrate for device bonding as claimed in claim 4, wherein the solder layer (iv) is composed of a solder said solder containing Sn or In as a main component and having an Au content of less than 20% by weight.

6. (Previously Presented) A substrate for device bonding, which is produced by the process of claim 4.

7. (Original) A process for producing a device-bonded substrate, comprising placing a device with an electrode on the solder layer of the substrate for device bonding of claim 1 in such a manner that the electrode is brought into contact with the solder layer and then reflow soldering is applied to the device.

8. (Original) A device-bonded substrate, which is produced by the process of claim 7.

9. (Currently Amended) The substrate for device bonding as claimed in claim 2, wherein the substrate having an ~~Au~~ said Au electrode layer on its surface is a metallized substrate in which a first undercoating metal layer containing Ti as a main component, a second undercoating metal layer containing Pt as a main component and an ~~electrode~~ said electrode layer composed of Au are laminated in this order on a ceramic substrate containing aluminum nitride as a main component.

10. (Previously Presented) A substrate for device bonding, which is produced by the process of claim 5.